Features

- Temperature ranges
  - Automotive -A: –40 °C to 85 °C
  - Automotive-E: –40 °C to 125 °C
- High speed
  - t_{AA} = 10 ns
- Low active power
  - 360 mW (max)
- 2.0 V data retention
- Automatic power down when deselected
- TTL-compatible inputs and outputs
- Easy memory expansion with $\overline{CE}$ and $\overline{OE}$ features

Functional Description

The CY7C1049CV33 Automotive is a high performance CMOS Static RAM organized as 524,288 words by eight bits. Easy memory expansion is provided by an active LOW Chip Enable ($\overline{CE}$), an active LOW Output Enable ($\overline{OE}$), and three-state drivers. Writing to the device is accomplished by taking Chip Enable ($\overline{CE}$) and Write Enable ($\overline{WE}$) inputs LOW. Data on the eight I/O pins (I/O$_0$ through I/O$_7$) is then written into the location specified on the address pins (A$_0$ through A$_{18}$).
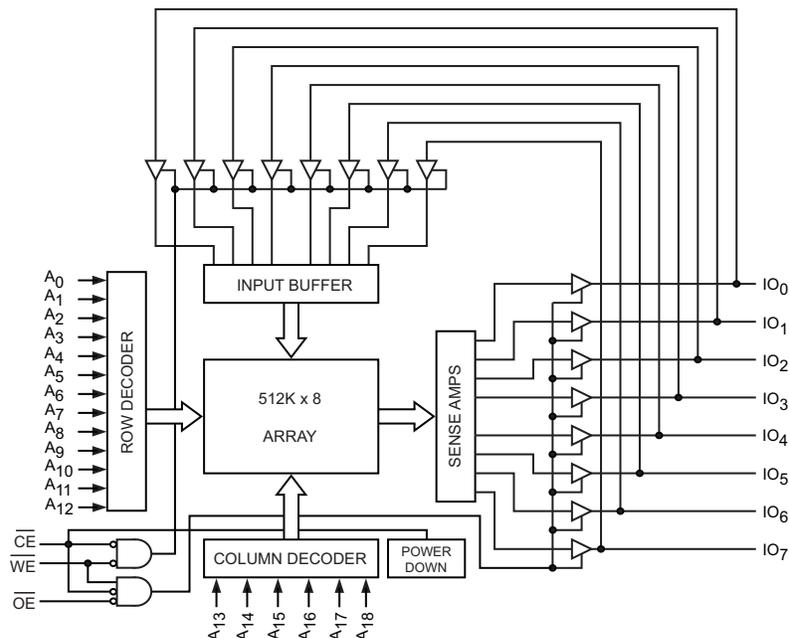
Reading from the device is accomplished by taking Chip Enable ($\overline{CE}$) and Output Enable ($\overline{OE}$) LOW while forcing Write Enable ($\overline{WE}$) HIGH. Under these conditions, the contents of the memory location specified by the address pins appear on the I/O pins.

The eight input and output pins (I/O$_0$ through I/O$_7$) are placed in a high impedance state when the device is deselected ($\overline{CE}$ HIGH), the outputs are disabled ($\overline{OE}$ HIGH), or during a write operation ($\overline{CE}$ LOW, and $\overline{WE}$ LOW).

The CY7C1049CV33 Automotive is available in standard 400-mil-wide 36-pin SOJ package and 44-pin TSOP II package with center power and ground (revolutionary) pinout.

For best practice recommendations, refer to the Cypress application note AN1064, SRAM System Guidelines.

Logic Block Diagram

Contents

Selection Guide

Description		-10	-12	-15	Unit
Maximum Access Time		10	12	15	ns
Maximum Operating Current	Automotive-A	100	95	–	mA
	Automotive-E	–	–	95	mA
Maximum CMOS Standby Current	Automotive-A	10	10	–	mA
	Automotive-E	–	–	15	mA

Pin Configuration

Figure 1. 36-pin SOJ (Top View)
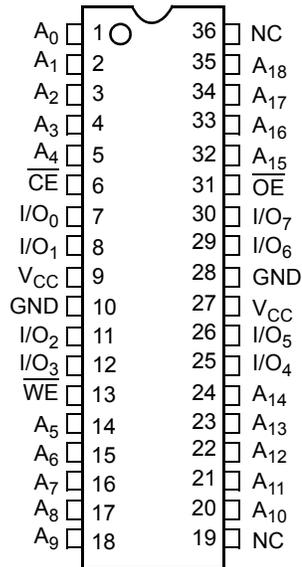
Figure 2. 44-pin TSOP II (Top View)

36-pin SOJ (Top View)	44-pin TSOP II (Top View)
A_0 1 — 36 NC A_1 2 — 35 A_{18} A_2 3 — 34 A_{17} A_3 4 — 33 A_{16} A_4 5 — 32 A_{15} $\overline{CE}$ 6 — 31 $\overline{OE}$ I/O_0 7 — 30 I/O_7 I/O_1 8 — 29 I/O_6 V_{CC} 9 — 28 GND GND 10 — 27 V_{CC} I/O_2 11 — 26 I/O_5 I/O_3 12 — 25 I/O_4 $\overline{WE}$ 13 — 24 A_{14} A_5 14 — 23 A_{13} A_6 15 — 22 A_{12} A_7 16 — 21 A_{11} A_8 17 — 20 A_{10} A_9 18 — 19 NC	NC 1 — 44 NC NC 2 — 43 NC A_0 3 — 42 NC A_1 4 — 41 A_{18} A_2 5 — 40 A_{17} A_3 6 — 39 A_{16} A_4 7 — 38 A_{15} $\overline{CE}$ 8 — 37 $\overline{OE}$ I/O_0 9 — 36 I/O_7 I/O_1 10 — 35 I/O_6 V_{CC} 11 — 34 V_{SS} V_{SS} 12 — 33 V_{CC} I/O_2 13 — 32 I/O_5 I/O_3 14 — 31 I/O_4 $\overline{WE}$ 15 — 30 A_{14} A_5 16 — 29 A_{13} A_6 17 — 28 A_{12} A_7 18 — 27 A_{11} A_8 19 — 26 A_{10} A_9 20 — 25 NC NC 21 — 24 NC NC 22 — 23 NC

Pin Definitions

Pin Name	36 SOJ Pin Number	44 TSOP II Pin Number	I/O Type	Description
A_0–A_{18}	1–5, 14–18, 20–24, 32–35	3–7, 16–20, 26–30, 38–41	Input	**Address inputs used to select one of the address locations.**
I/O_0–I/O_7	7, 8, 11, 12, 25, 26, 29, 30	9, 10, 13, 14, 31, 32, 35, 36	Input/Output	**Bidirectional data I/O lines.** Used as input or output lines depending on operation
NC[1]	19, 36	1, 2, 21, 22, 23, 24, 25, 42, 43, 44	No Connect	**No connects.** This pin is not connected to the die
$\overline{WE}$	13	15	Input/Control	**Write Enable input, active LOW.** When selected LOW, a WRITE is conducted. When selected HIGH, a READ is conducted.
$\overline{CE}$	6	8	Input/Control	**Chip Enable input, active LOW.** When LOW, selects the chip. When HIGH, deselects the chip.
$\overline{OE}$	31	37	Input/Control	**Output Enable, active LOW.** Controls the direction of the I/O pins. When LOW, the I/O pins are allowed to behave as outputs. When deasserted HIGH, I/O pins are three-stated, and act as input data pins.
V_{SS}, GND	10, 28	12, 34	Ground	**Ground for the device.** Should be connected to ground of the system.
V_{CC}	9, 27	11, 33	Power Supply	**Power supply inputs to the device.**

Note
1. NC pins are not connected on the die.

[+] Feedback

Maximum Ratings

Exceeding maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage Temperature .... –65 °C to +150 °C

Ambient Temperature with
Power Applied .... –55 °C to +125 °C

Supply Voltage on V_{CC} to Relative GND[2]–0.5 V to +4.6 VDC

Voltage Applied to Outputs
in High Z State[2] .... –0.5 V to V_{CC} + 0.5 V

Input Voltage[2] .... –0.5 V to V_{CC} + 0.5 V

Current into Outputs (LOW) .... 20 mA

Operating Range

Range	Ambient Temperature	V_{CC}
Automotive-A	–40 °C to +85 °C	3.3 V $\pm$ 0.3 V
Automotive-E	–40 °C to +125 °C	

Electrical Characteristics

Over the Operating Range

Parameter	Description	Test Conditions		-10 Min	-10 Max	-12 Min	-12 Max	-15 Min	-15 Max	Unit
V_{OH}	Output HIGH Voltage	V_{CC} = Min; I_{OH} = –4.0 mA		2.4	–	2.4	–	2.4	–	V
V_{OL}	Output LOW Voltage	V_{CC} = Min; I_{OL} = 8.0 mA		–	0.4	–	0.4	–	0.4	V
V_{IH}	Input HIGH Voltage			2.0	V_{CC} + 0.3	2.0	V_{CC} + 0.3	2.0	V_{CC} + 0.3	V
V_{IL}	Input LOW Voltage[2]			–0.3	0.8	–0.3	0.8	–0.3	0.8	V
I_{IX}	Input Load Current	GND $\leq V_I \leq V_{CC}$	Auto-A	–1	+1	–1	+1	–	–	µA
			Auto-E	–	–	–	–	–20	+20	
I_{CC}	V_{CC} Operating Supply Current	V_{CC} = Max, f = f_{MAX} = 1/t_{RC}	Auto-A	–	100	–	95	–	–	mA
			Auto-E	–	–	–	–	–	95	
I_{SB1}	Automatic CE Power Down Current —TTL Inputs	Max. V_{CC}, $\overline{CE} \geq V_{IH}$; $V_{IN} \geq V_{IH}$ or $V_{IN} \leq V_{IL}$, f = f_{MAX}	Auto-A	–	40	–	40	–	–	mA
			Auto-E	–	–	–	–	–	45	mA
I_{SB2}	Automatic CE Power Down Current —CMOS Inputs	Max. V_{CC}, $\overline{CE} \geq V_{CC}$ – 0.3 V, $V_{IN} \geq V_{CC}$ – 0.3 V, or $V_{IN} \leq 0.3$ V, f = 0	Auto-A	–	10	–	10	–	–	mA
			Auto-E	–	–	–	–	–	15	mA

Capacitance

Tested initially and after any design or process changes that may affect these parameters.

Parameter[3]	Description	Test Conditions	Max	Unit
C_{IN}	Input Capacitance	T_A = 25 °C, f = 1 MHz, V_{CC} = 3.3 V	8	pF
C_{OUT}	I/O Capacitance		8	pF

Thermal Resistance

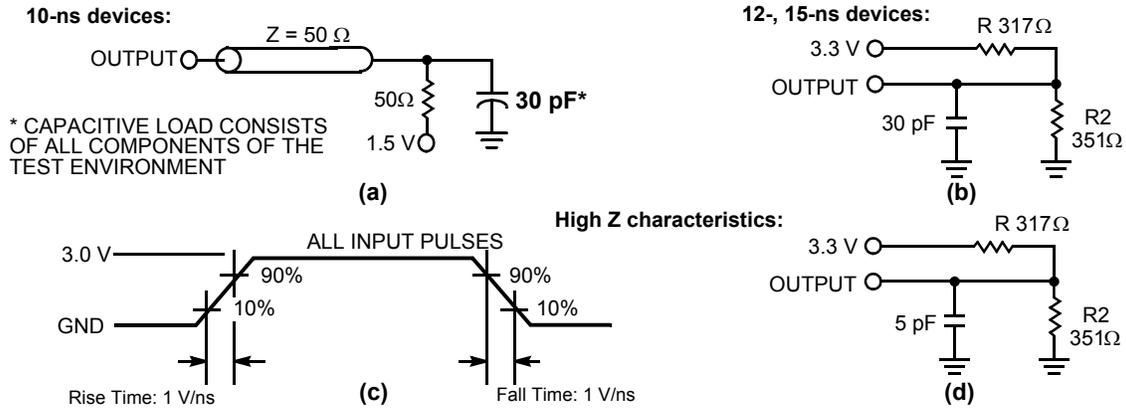Tested initially and after any design or process changes that may affect these parameters.

Parameter[3]	Description	Test Conditions	36-pin SOJ	44-pin TSOP-II	Unit
Θ_{JA}	Thermal Resistance (Junction to Ambient)	Test conditions follow standard test methods and procedures for measuring thermal impedance, per EIA / JESD51.	46.51	41.66	°C/W
Θ_{JC}	Thermal Resistance (Junction to Case)		18.8	10.56	°C/W

Notes
2. V_{IL} (min) = –2.0 V and V_{IH}(max) = V_{CC} + 0.5 V for pulse durations of less than 20 ns.
3. Tested initially and after any design or process changes that may affect these parameters.

[+] Feedback

Figure 3. AC Test Loads and Waveforms [4]

10-ns devices:

OUTPUT Z = 50 Ω

50Ω

30 pF*

1.5 V

* CAPACITIVE LOAD CONSISTS OF ALL COMPONENTS OF THE TEST ENVIRONMENT

(a)

12-, 15-ns devices:

R 317Ω

3.3 V

OUTPUT

30 pF

R2 351Ω

(b)

ALL INPUT PULSES

3.0 V

90%

10%

GND

Rise Time: 1 V/ns

90%

10%

Fall Time: 1 V/ns

(c)

High Z characteristics:

R 317Ω

3.3 V

OUTPUT

5 pF

R2 351Ω

(d)

Notes
4. AC characteristics (except High Z) for 10 ns parts are tested using the load conditions shown in Figure 3 (a). All other speeds are tested using the Thevenin load shown in Figure 3 (b). High Z characteristics are tested for all speeds using the test load shown in Figure 3 (d).

[+] Feedback

AC Switching Characteristics

Over the Operating Range [5]

Parameter	Description	-10		-12		-15		Unit
		Min	Max	Min	Max	Min	Max	
Read Cycle								
t_{power}[6]	V_{CC}(typical) to the first access	100	–	100	–	100	–	µs
t_{RC}	Read Cycle Time	10	–	12	–	15	–	ns
t_{AA}	Address to Data Valid	–	10	–	12	–	15	ns
t_{OHA}	Data Hold from Address Change	3	–	3	–	–	3	ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid	–	10	–	12	–	15	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid	–	5	–	6	–	7	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z	0	–	0	–	0	–	ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[7, 8]	–	5	–	6	–	7	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z[8]	3	–	3	–	3	–	ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z[7, 8]	–	5	–	6	–	7	ns
t_{PU}	$\overline{CE}$ LOW to Power Up	0	–	0	–	0	–	ns
t_{PD}	$\overline{CE}$ HIGH to Power Down	–	10	–	12	–	15	ns
Write Cycle [9, 10]								
t_{WC}	Write Cycle Time	10	–	12	–	15	–	ns
t_{SCE}	$\overline{CE}$ LOW to Write End	7	–	8	–	10	–	ns
t_{AW}	Address Setup to Write End	7	–	8	–	10	–	ns
t_{HA}	Address Hold from Write End	0	–	0	–	0	–	ns
t_{SA}	Address Setup to Write Start	0	–	0	–	0	–	ns
t_{PWE}	$\overline{WE}$ Pulse Width	7	–	8	–	10	–	ns
t_{SD}	Data Setup to Write End	5	–	6	–	7	–	ns
t_{HD}	Data Hold from Write End	0	–	0	–	0	–	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z[8]	3	–	3	–	3	–	ns
t_{HZWE}	$\overline{WE}$ LOW to High Z[7, 8]	–	5	–	6	–	7	ns

Notes
5. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V.
6. t_{POWER} gives the minimum amount of time that the power supply should be at stable, typical V_{CC} values until the first memory access can be performed.
7. t_{HZOE}, t_{HZCE}, and t_{HZWE} are specified with a load capacitance of 5 pF as in part (d) of Figure 3 on page 5. Transition is measured ±500 mV from steady-state voltage.
8. At any temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any device.
9. The internal Write time of the memory is defined by the overlap of $\overline{CE}$ LOW, and $\overline{WE}$ LOW. $\overline{CE}$ and $\overline{WE}$ must be LOW to initiate a Write, and the transition of either of these signals can terminate the Write. The input data setup and hold timing should be referenced to the leading edge of the signal that terminates the Write.
10. The minimum Write cycle time for Write Cycle No. 3 ($\overline{WE}$ controlled, $\overline{OE}$ LOW) is the sum of t_{HZWE} and t_{SD}.

[+] Feedback

Switching Waveforms

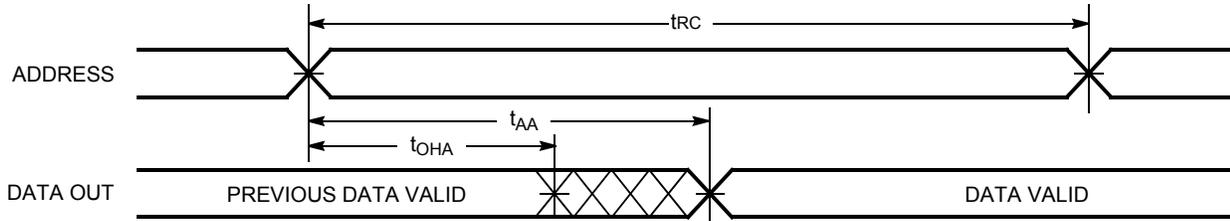**Figure 4. Read Cycle No. 1** (Address Transition Controlled) [11, 12]

Figure 5. Read Cycle No. 2 ($\overline{OE}$ Controlled) [12, 13]
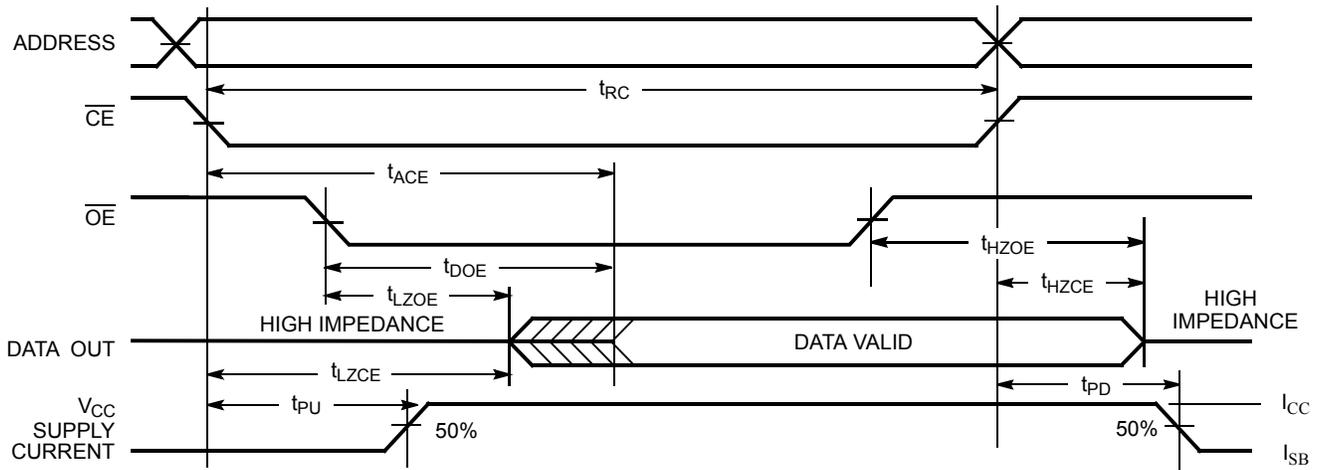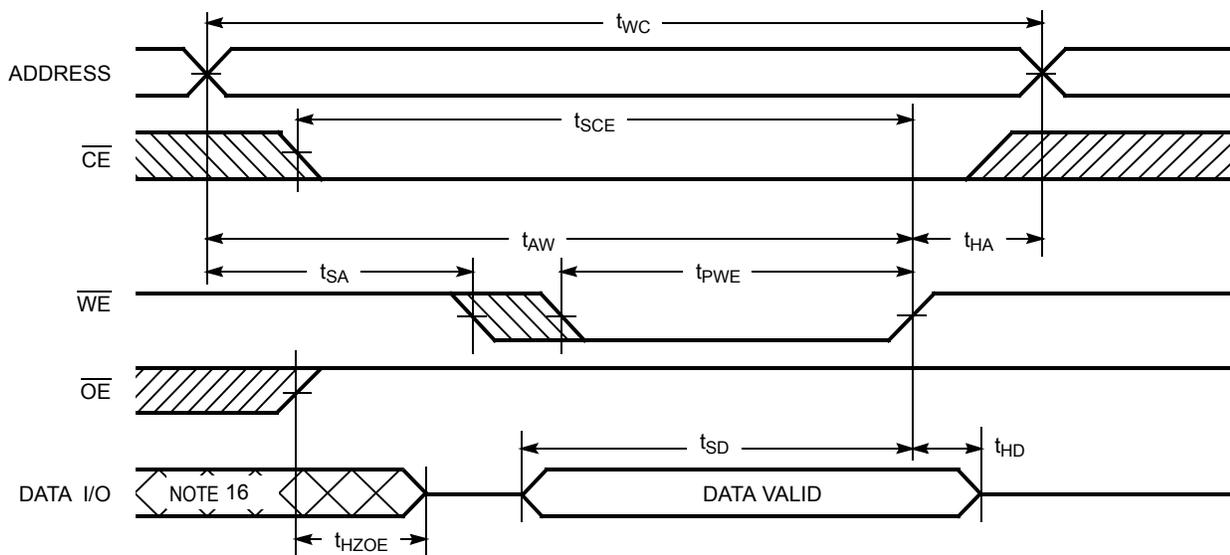

Figure 6. Write Cycle No. 1 ($\overline{WE}$ Controlled, $\overline{OE}$ HIGH During Write) [14, 15]


Notes
11. Device is continuously selected. $\overline{OE}$, $\overline{CE}$ = V_{IL}.
12. $\overline{WE}$ is HIGH for read cycles.
13. Address valid before or similar to $\overline{CE}$ transition LOW.
14. Data I/O is high impedance if $\overline{OE}$ = V_{IH}.
15. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ HIGH, the output remains in high impedance state.
16. During this period, the I/Os are in output state. Do not apply input signals.

[+] Feedback

Switching Waveforms (continued)

Figure 7. Write Cycle No. 2 ($\overline{\text{WE}}$ Controlled, $\overline{\text{OE}}$ LOW) [17]
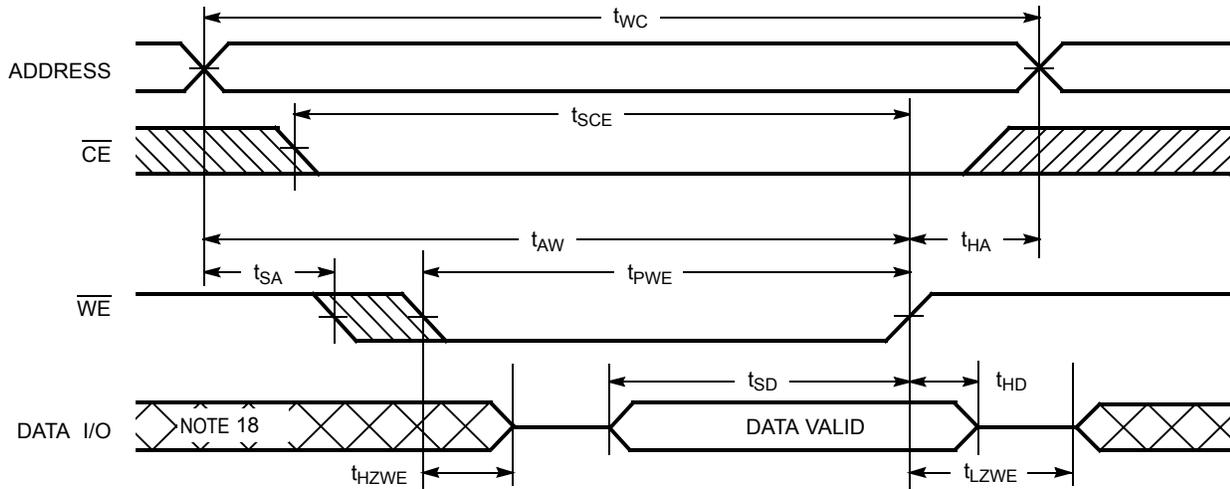
Truth Table

$\overline{\text{CE}}$	$\overline{\text{OE}}$	$\overline{\text{WE}}$	I/O$_0$–I/O$_7$	Mode	Power
H	X	X	High Z	Power Down	Standby (I_{SB})
L	L	H	Data Out	Read	Active (I_{CC})
L	X	L	Data In	Write	Active (I_{CC})
L	H	H	High Z	Selected, Outputs Disabled	Active (I_{CC})

Notes
17. If $\overline{\text{CE}}$ goes HIGH simultaneously with $\overline{\text{WE}}$ HIGH, the output remains in high impedance state.
18. During this period, the I/Os are in output state. Do not apply input signals.

[+] Feedback

Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
10	CY7C1049CV33-10VXA	51-85090	36-pin (400-Mil) Molded SOJ (Pb-free)	Automotive-A
12	CY7C1049CV33-12ZSXA	51-85087	44-pin TSOP II (Pb-free)	Automotive-A
15	CY7C1049CV33-15VXE	51-85090	36-pin (400-Mil) Molded SOJ (Pb-free)	Automotive-E
	CY7C1049CV33-15ZSXE	51-85087	44-pin TSOP II (Pb-free)	Automotive-E

Ordering Code Definitions

CY 7C 1 04 9 C V33 - XX XX X X

Temperature Range: X = A or E
A = Automotive-A or E = Automotive-E

X = Pb-free; X Absent = Leaded

Package Type: XX = V or ZS
V = 36-pin Molded SOJ
ZS = 44-pin TSOP II

Speed Grade: XX = 10 ns or 12 ns or 15 ns

V33 = 3.0 V to 3.6 V

Process Technology: C = 150 nm

Data width: × 8-bits

4-Mbit density

Fast Asynchronous SRAM

Marketing Code: 7C = SRAMs

Company ID: CY = Cypress

[+] Feedback
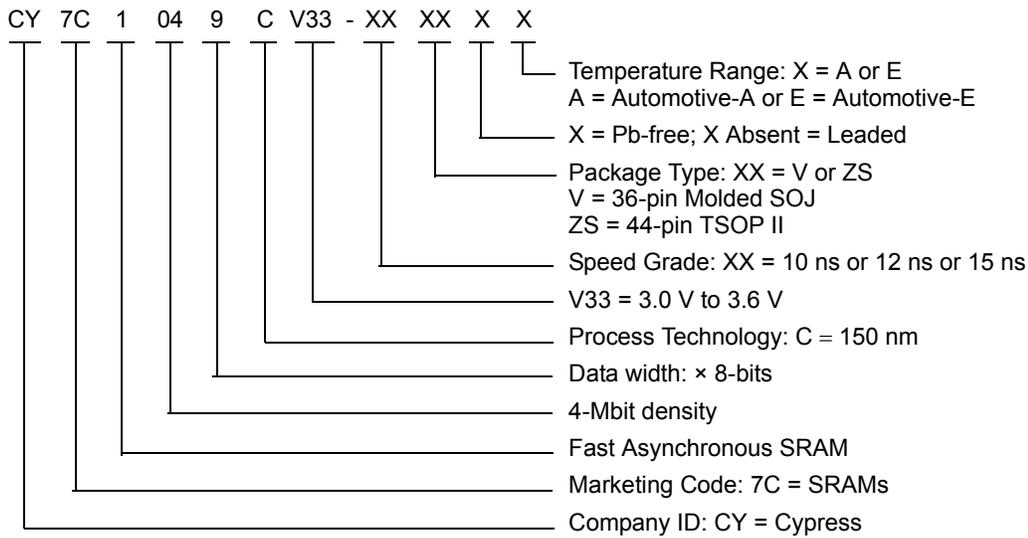
Package Diagrams

Figure 8. 36-pin (400-Mil) Molded SOJ, 51-85090
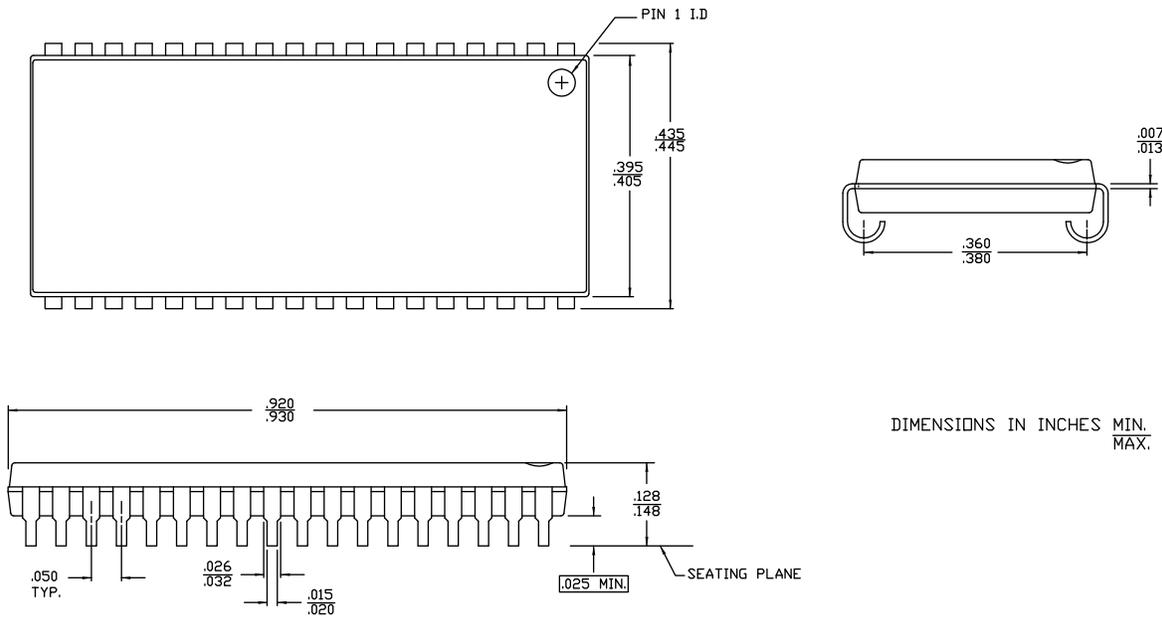
51-85090 *E

Figure 9. 44-pin TSOP II, 51-85087

51-85087 *C

[+] Feedback
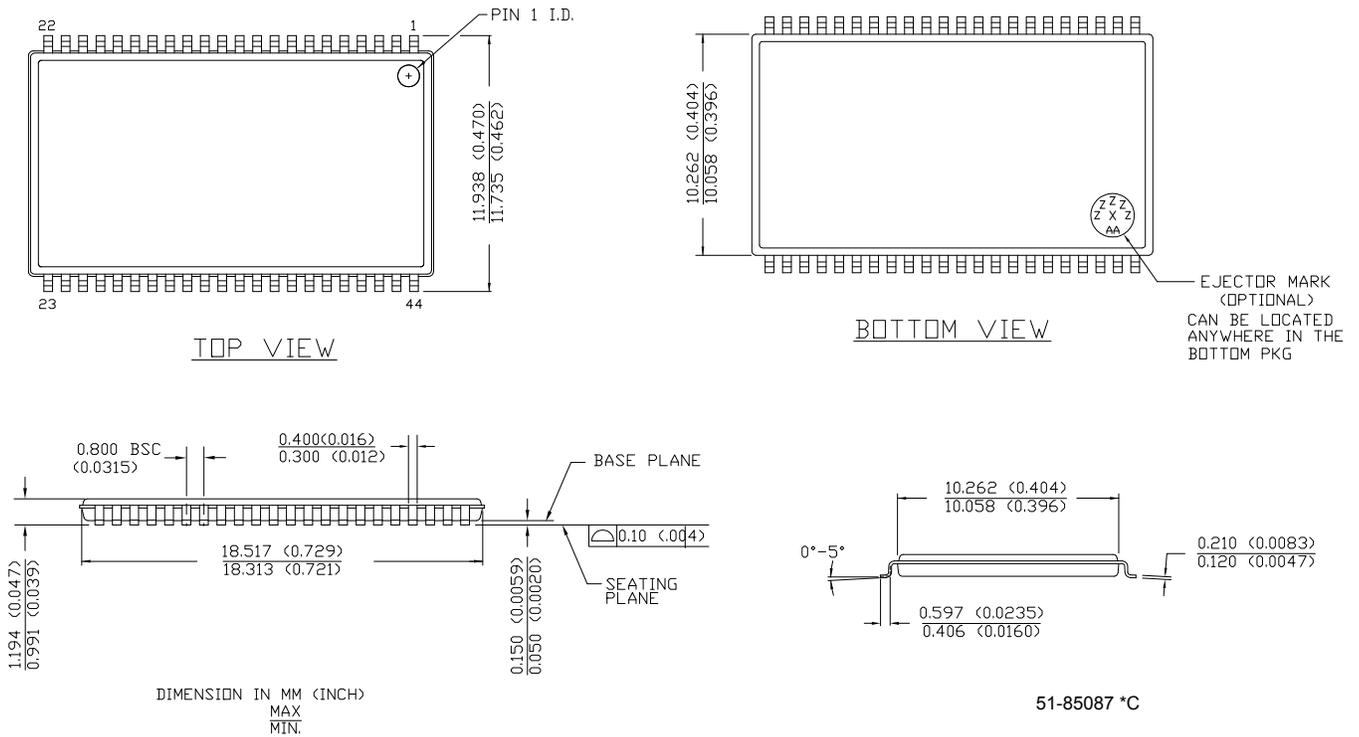
Acronyms

Acronym	Description
CMOS	complementary metal oxide semiconductor
$\overline{CE}$	Chip Enable
$\overline{OE}$	Output Enable
RAM	Random Access Memory
I/O	Input/Output
SOJ	small outline J-lead
TTL	transistor-transistor logic
TSOP	thin small outline package
$\overline{WE}$	Write Enable

Document Conventions

Units of Measure

Symbol	Unit of Measure
Ω	ohms
ns	nano seconds
V	Volts
µs	micro seconds
µA	micro Amperes
mA	milli Amperes
mm	milli meter
ms	milli seconds
MHz	Mega Hertz
pF	pico Farad
%	percent
mW	milli Watts
W	Watts
°C	degree Celcius

[+] Feedback

Document History Page

Document Title: CY7C1049CV33 Automotive 4-Mbit (512 K × 8) Static RAM Document Number: 001-67511				
Rev.	ECN	Orig. of Change	Submission Date	Description of Change
**	3186792	PRAS	03/03/2011	Separation of the automotive datasheet from CY7C1049CV33 spec no. 38-05006 Rev. *J. Further rev of 38-05006 would include only industrial / commercial parts.

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